

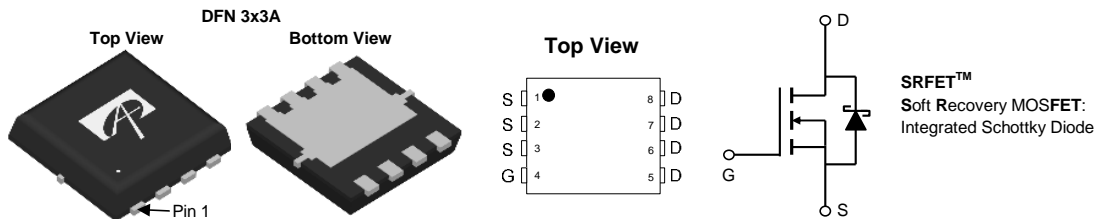
General Description

SRFET™ AON7702A uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

Product Summary

| | |
|------------------------------------|----------------|
| V_{DS} | 30V |
| I_D (at $V_{GS}=10V$) | 36A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | < 10m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) | < 13m Ω |

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|------------------|-------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current | I_D | $T_C=25^\circ\text{C}$ | 36 |
| | | $T_C=100^\circ\text{C}$ | 22 |
| Pulsed Drain Current ^C | I_{DM} | 80 | A |
| Continuous Drain Current | I_{DSM} | $T_A=25^\circ\text{C}$ | 13.5 |
| | | $T_A=70^\circ\text{C}$ | 11 |
| Avalanche Current ^C | I_{AS}, I_{AR} | 15 | A |
| Avalanche energy $L=0.1\text{mH}$ ^C | E_{AS}, E_{AR} | 11 | mJ |
| Power Dissipation ^B | P_D | $T_C=25^\circ\text{C}$ | 23 |
| | | $T_C=100^\circ\text{C}$ | 9 |
| Power Dissipation ^A | P_{DSM} | $T_A=25^\circ\text{C}$ | 3.1 |
| | | $T_A=70^\circ\text{C}$ | 2 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|---------------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 30 | 40 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A D} | | Steady-State | 60 | 75 |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 4.5 | 5.4 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|-----|------|------------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} =0V T _J =125°C | | | 0.5 100 | mA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±12V | | | 100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 1.2 | 1.65 | 2.1 | V |
| I _{D(ON)} | On state drain current | V _{GS} =10V, V _{DS} =5V | 80 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =10V, I _D =13A T _J =125°C | | 8.2 | 10 | mΩ |
| | | V _{GS} =4.5V, I _D =11A | | 9.9 | 13 | |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =13A | | 80 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.4 | 0.7 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 30 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =15V, f=1MHz | 930 | 1170 | 1400 | pF |
| C _{oss} | Output Capacitance | | 90 | 128 | 170 | pF |
| C _{riss} | Reverse Transfer Capacitance | | 45 | 89 | 125 | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 0.7 | 1.4 | 2.1 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _{g(10V)} | Total Gate Charge | V _{GS} =10V, V _{DS} =15V, I _D =13A | 16 | 20 | 24 | nC |
| Q _{g(4.5V)} | Total Gate Charge | | 7 | 8.7 | 10.5 | nC |
| Q _{gs} | Gate Source Charge | | | 3.2 | | nC |
| Q _{gd} | Gate Drain Charge | | | 3 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =10V, V _{DS} =15V, R _L =1.2Ω, R _{GEN} =3Ω | | 6 | | ns |
| t _r | Turn-On Rise Time | | | 2.4 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 23 | | ns |
| t _f | Turn-Off Fall Time | | | 4 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =13A, dI/dt=500A/μs | 5.5 | 7 | 8.5 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =13A, dI/dt=500A/μs | 5 | 6.5 | 8 | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

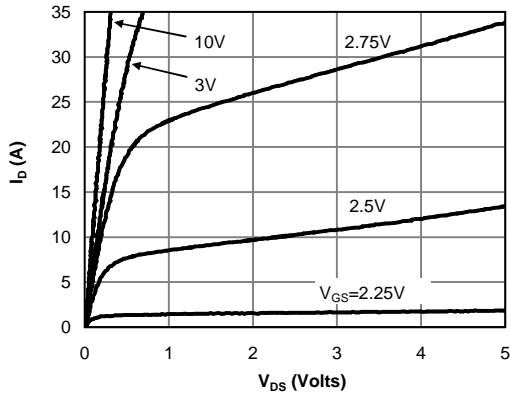


Fig 1: On-Region Characteristics (Note E)

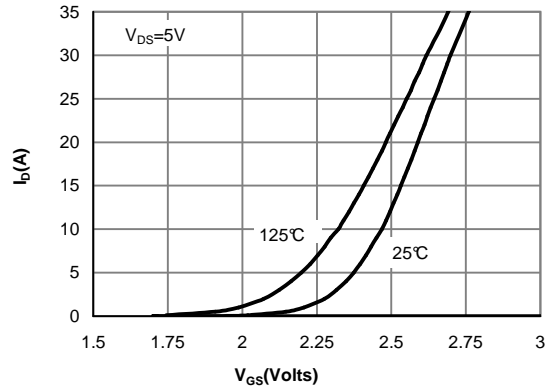


Figure 2: Transfer Characteristics (Note E)

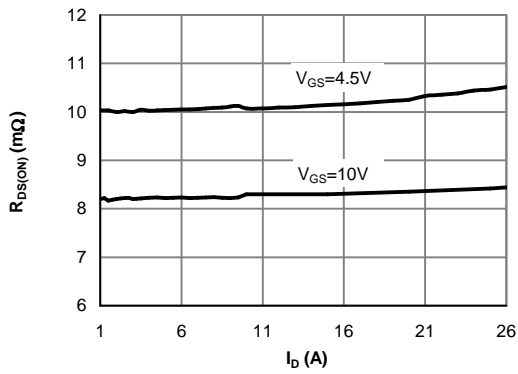


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

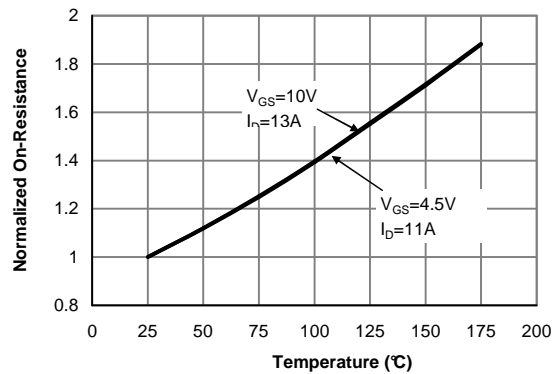


Figure 4: On-Resistance vs. Junction Temperature (Note E)

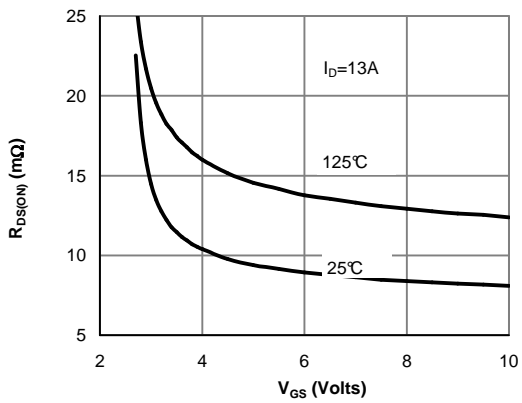


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

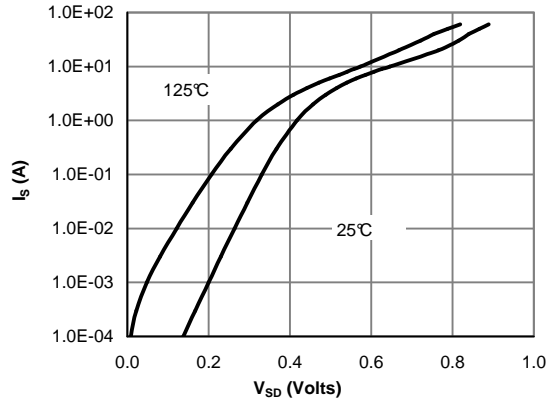


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

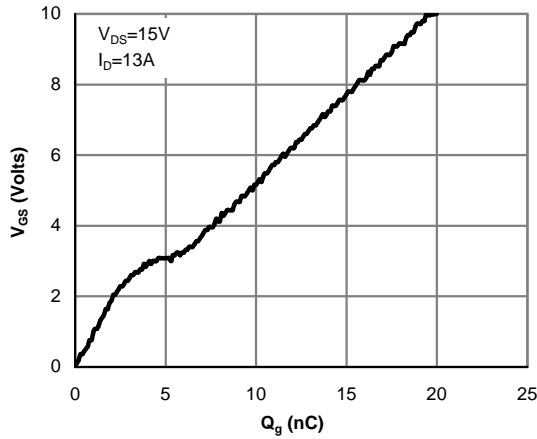


Figure 7: Gate-Charge Characteristics

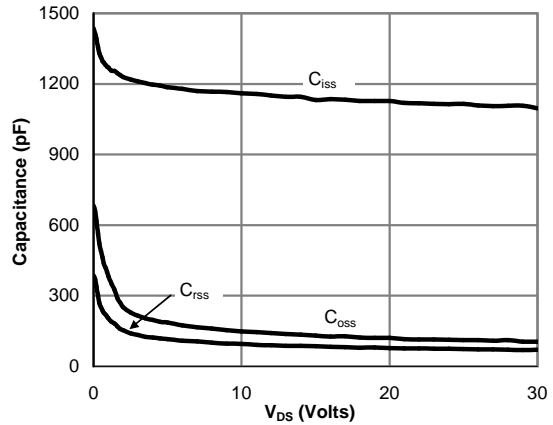


Figure 8: Capacitance Characteristics

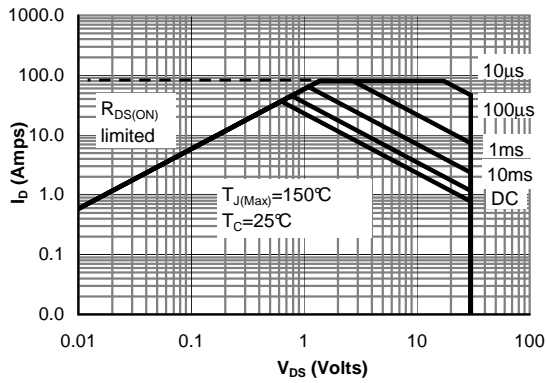


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

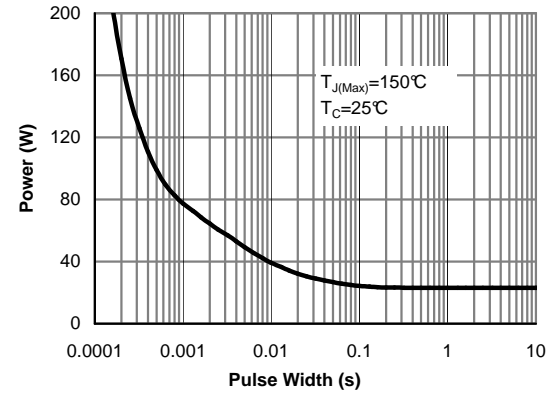


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

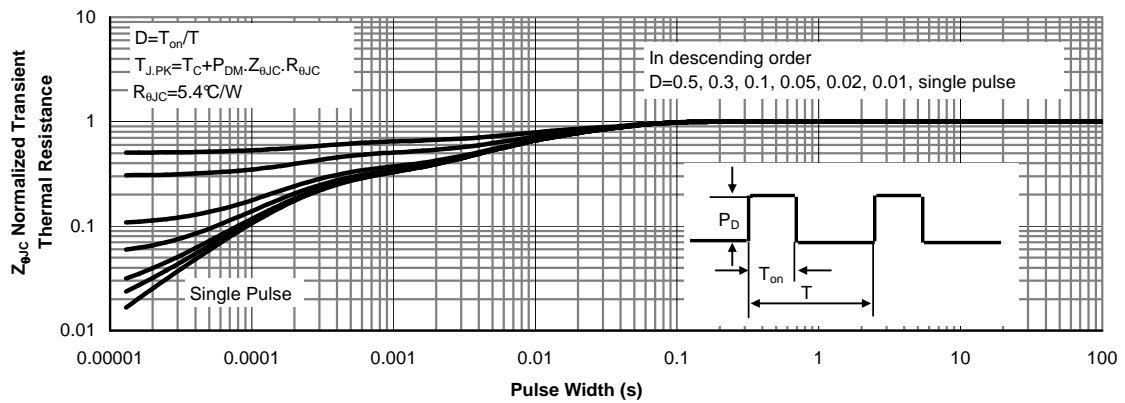


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

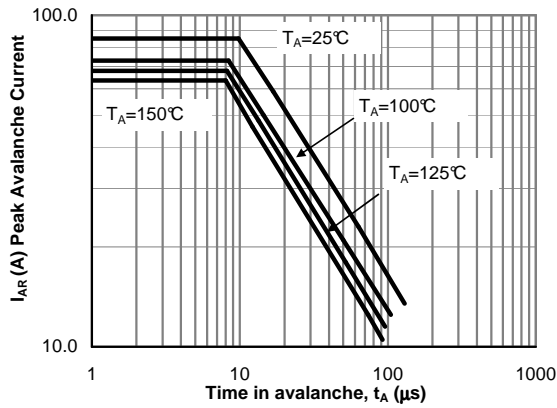


Figure 12: Single Pulse Avalanche capability (Note C)

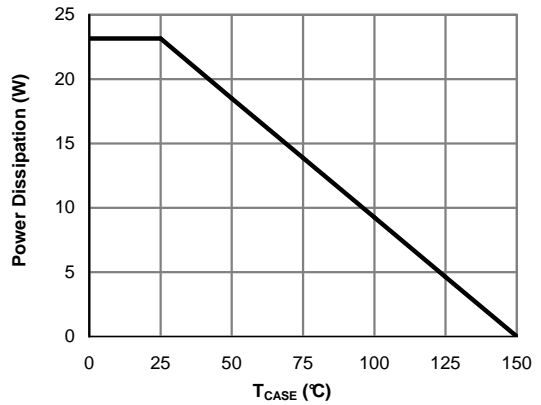


Figure 13: Power De-rating (Note F)

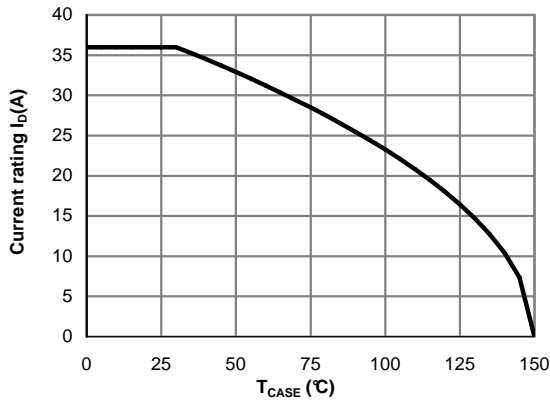


Figure 14: Current De-rating (Note F)

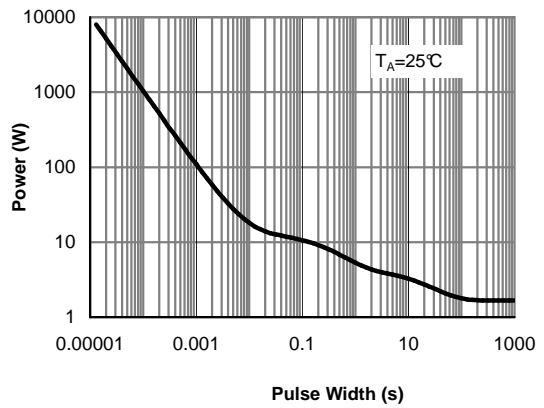


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

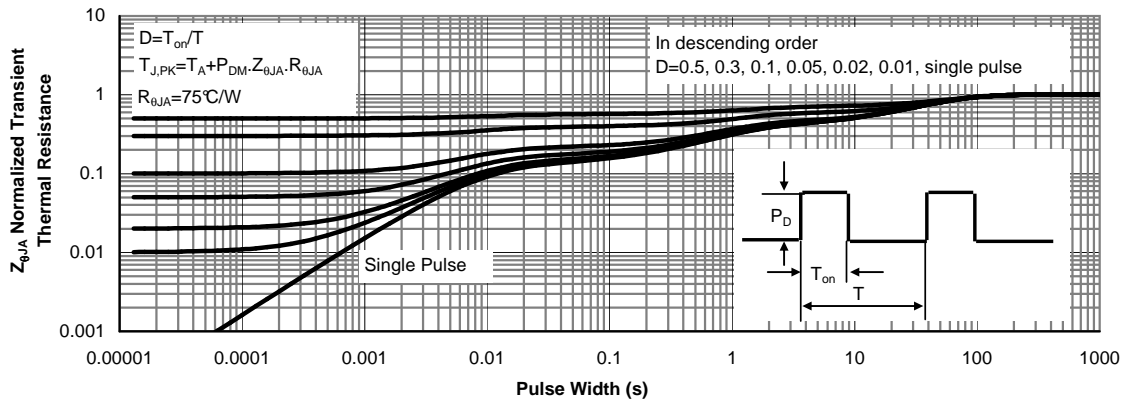
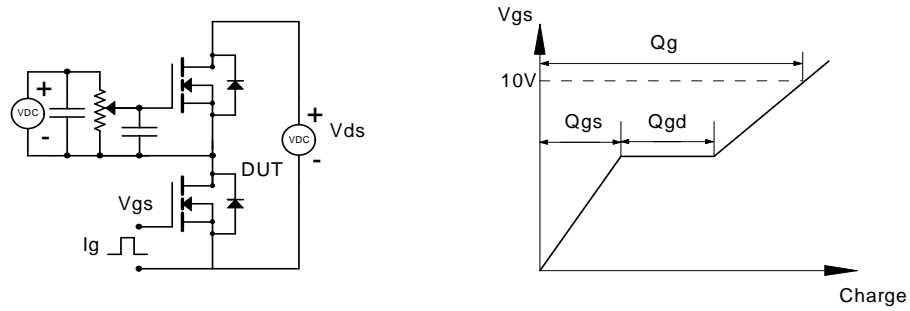
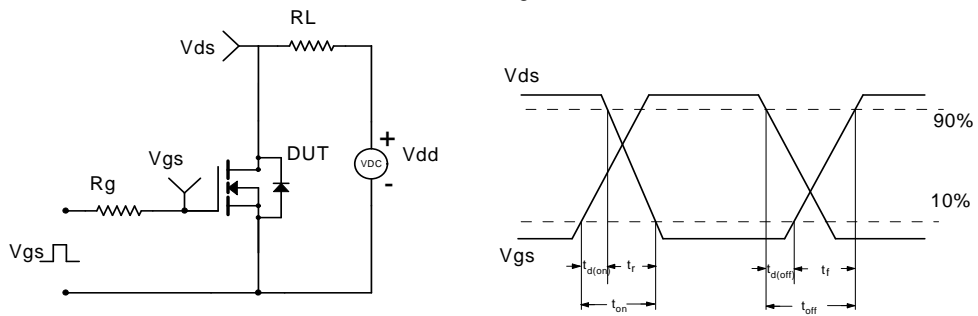


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

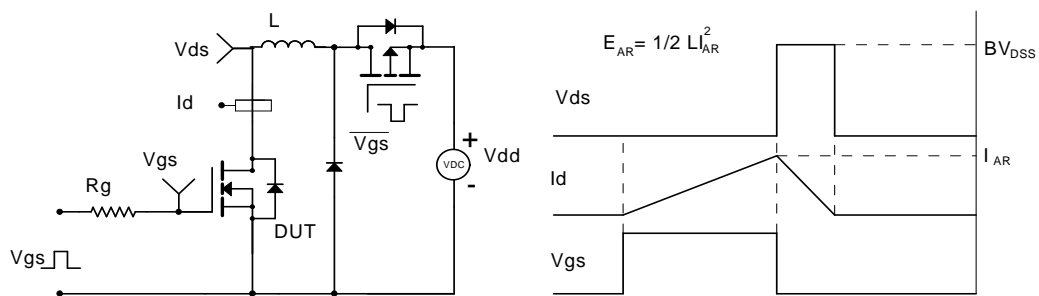
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

